Transmitted herewith for filing is the patent application of:

I HEREBY CERTIFY THIS PAPER OR FEE IS BEING DEPOSITED WITH THE U.S. POSTAL SERVICE "EXPRESS MAIL POST OFFICE TO ADDRESSEE" SERVICE UNDER 37 CFR 1.10 ON THE DATE INDICATED BELOW AND IS ADDRESSED TO: MS PATENT APPLICATION, COMMISSIONER FOR PATENTS, PO BOX 1450, ALEXANDRIA, VA 22313-

EXPRESS MAIL NO: EV322694470US

DATE OF DEPOSIT: Dec mber 30, 2003

NAME: <u>Justin Goree</u>

SIGNATURE:

Inventors:

Agnelo MAGRI' Ferruccio FRISINA Giuseppe FERLA Marco CAMALLERI

For:

[X]

VERTICAL-CONDUCTION AND PLANAR-STRUCTURE MOS DEVICE WITH A DOUBLE THICKNESS OF GATE OXIDE AND METHOD FOR REALIZING POWER VERTICAL MOS TRANSISTORS WITH IMPROVED STATIC AND DYNAMIC

PERFORMANCES AND HIGH SCALING DOWN DENSITY

## **Enclosed are:**

Patent Application: <u>17</u> pages, <u>14</u> claims <u>8</u> sheets of drawings

The suggested drawing figure to be published is FIG. 6C. A Preliminary Amendment (with \_2\_ replacement drawing sheets).

Assignee info:

STMicroelectronics S.r.l. Via C. Olivetti, 2, 20041 Agrate Brianza (MI), Italy Address:

Country of Incorporation: Italy

Applicant claims priority benefit to the following foreign application(s):

Country: Europe

Application No.: Filing Date:

02425803.0 December 30, 2003

The Declaration and Filing Fee are **NOT ENCLOSED**.

[X] Name, Address and Citizenship of Inventor(s) is as follows:

> Angelo MAGRI', Via F. Cairoli, 28/B, I-95032 Belpasso (CT), Italy Citizen of Italy

Ferruccio FRISINA, Via Tre Torri, 11, I-95030 Sant'Agata Li Battiati (LC), Italy Citizen of Italy

Giuseppe FERLA, Via Aci Castello, 12, I-95030 Catania, Italy Citizen of Italy

Marco CAMALLERI, c/o STMicroelectronics S.r.I., Via C. Olivetti 2, 20041 Agrat Brianza (MI), Italy

[X] PLEASE ADDRESS CORRESPONDENCE TO ATTORNEY OF RECORD: CHRISTOPHER F. REGAN

[X] Associate this file with Customer No. 27975.

Date: December 30, 2003

MICHAEL W. TAYLOR

Reg. No. 43,182